



30V N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17308Q3

FEATURES

- · Optimized for 5V Gate Drive
- Ultra Low Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3-mm × 3.3-mm Plastic Package

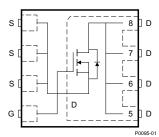
APPLICATIONS

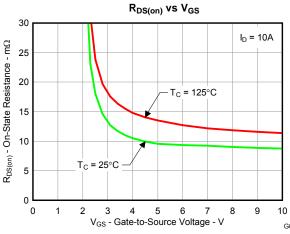
- · Notebook Point of Load
- Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.







PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage 30			V
Q_g	Gate Charge Total (4.5V)	3.9	3.9	
Q_{gd}	Gate Charge Gate to Drain 0.8			nC
		$V_{GS} = 3V$	12.5	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	9.4	mΩ
		V _{GS} = 8V 8.2		mΩ
$V_{GS(th)}$	Threshold Voltage 1.3			V

ORDERING INFORMATION

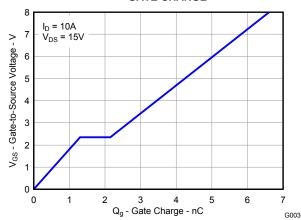
Device	Package	Media	Qty	Ship
CSD17308Q3	SON 3.3-mm × 3.3-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	٧
V_{GS}	Gate to Source Voltage	+10 / -8	V
	Continuous Drain Current, T _C = 25°C	47	Α
I _D	Continuous Drain Current ⁽¹⁾	13	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	78	Α
P_D	Power Dissipation ⁽¹⁾	2.7	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, Single Pulse $I_D=36A,L=0.1mH,R_G=25\Omega$	65	mJ

- (1) Typical $R_{\theta JA}=46^{\circ} C/W$ when mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300μs, duty cycle ≤2%

GATE CHARGE



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

 $(T_{\wedge} = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics	•				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +10 / -8V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9	1.3	1.8	V
		$V_{GS} = 3V, I_D = 10A$		12.5	16.5	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 10A$		9.4	11.8	mΩ
		$V_{GS} = 8V, I_D = 10A$		8.2	10.3	mΩ
g _{fs}	Transconductance	V _{DS} = 15V, I _D = 10A		37		S
Dynamic	: Characteristics					
C _{ISS}	Input Capacitance			540	700	рF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		280	365	рF
C _{RSS}	Reverse Transfer Capacitance			27	35	pF
R _g	Series Gate Resistance			0.9	1.8	Ω
Qg	Gate Charge Total (4.5V)			3.9	5.1	nC
Q_{gd}	Gate Charge Gate to Drain	\/ 45\/ L 40A		8.0		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 15V, I_{D} = 10A$		1.3		nC
Qg(th)	Gate Charge at Vth			0.7		nC
Q _{OSS}	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$		7.4		nC
t _{d(on)}	Turn On Delay Time			4.5		ns
t _r	Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 10A,$		5.7		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		9.9		ns
t _f	Fall Time			2.3		ns
Diode Cl	haracteristics					
V_{SD}	Diode Forward Voltage	I _{DS} = 10A, V _{GS} = 0V		0.85	1	V
Q _{rr}	Reverse Recovery Charge	V = 13V = 10A di/dt = 200A/va	9.3			nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 10A$, $di/dt = 300A/\mu s$		14.3		ns

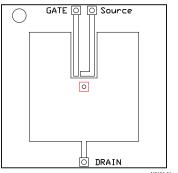
THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

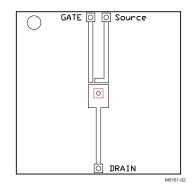
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			4.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			58	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 58^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 165^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

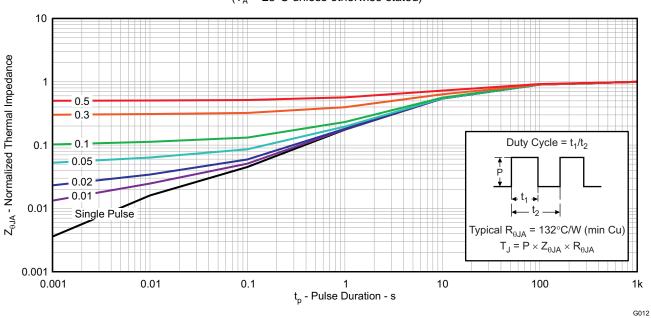


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25$ °C unless otherwise stated)

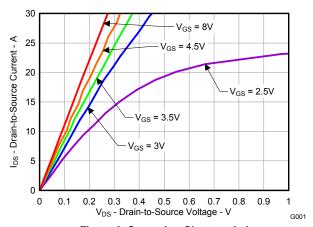


Figure 2. Saturation Characteristics

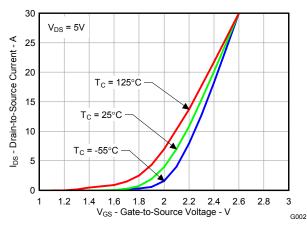


Figure 3. Transfer Characteristics

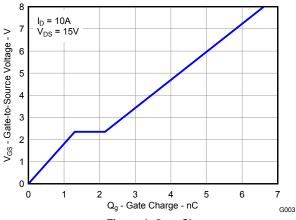
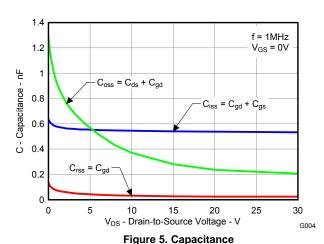
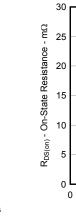
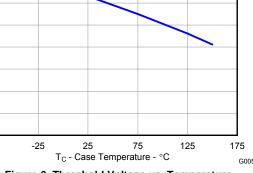


Figure 4. Gate Charge







 $I_D = 250 \mu A$

Figure 6. Threshold Voltage vs. Temperature

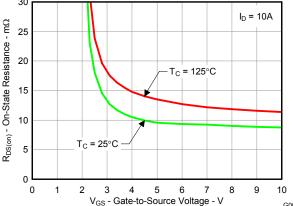


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

1.6

1.2

1

0.8

0.4

0.2

V_{GS(th)} - Threshold Voltage - V



TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

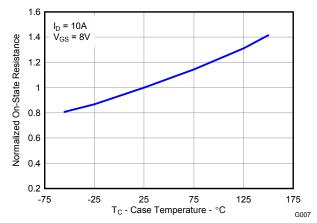


Figure 8. Normalized On-State Resistance vs. Temperature

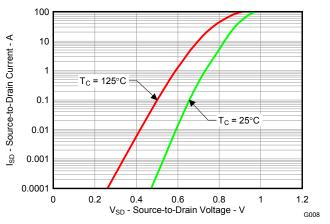


Figure 9. Typical Diode Forward Voltage

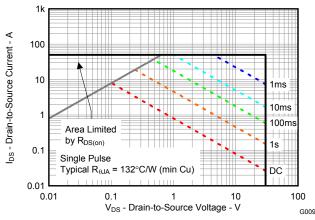


Figure 10. Maximum Safe Operating Area

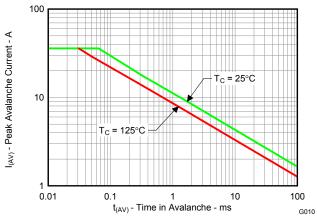


Figure 11. Single Pulse Unclamped Inductive Switching

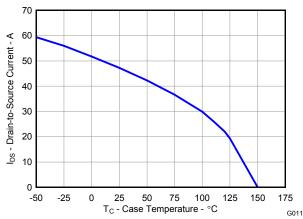
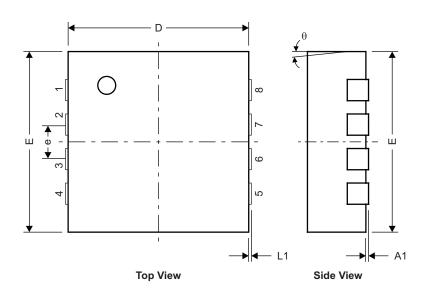


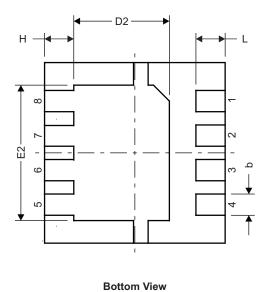
Figure 12. Maximum Drain Current vs. Temperature

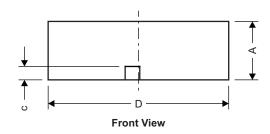


MECHANICAL DATA

Q3 Package Dimensions





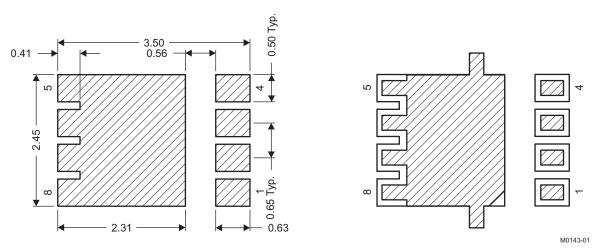


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DIM		MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.950	1.000	1.100	0.037	0.039	0.043	
A1	0.000	0.000	0.050	0.000	0.000	0.002	
b	0.280	0.340	0.400	0.011	0.013	0.016	
С	0.150	0.200	0.250	0.006	0.008	0.010	
D	3.200	3.300	3.400	0.126	0.130	0.134	
D1	_	_	1	_	-	_	
D2	1.650	1.750	1.800	0.065	0.069	0.071	
E	3.200	3.300	3.400	0.126	0.130	0.134	
E1	_	_	-	_	-	-	
E2	2.350	2.450	2.550	0.093	0.096	0.100	
е		0.650 TYP		0.026			
Н	0.35	0.450	0.550	0.014	0.018	0.022	
L	0.35	0.450	0.550	0.014	0.018	0.022	
L1	-	-	-	-	-	_	
θ	_	_	_	_	_	_	



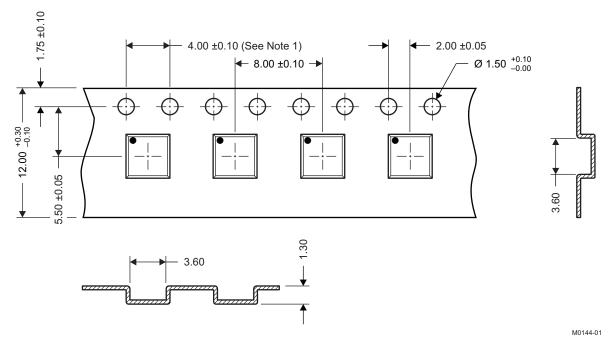
Recommended PCB Pattern



Note: All dimensions are in mm, unless otherwise specified.

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q3 Tape and Reel Information



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ±0.2

- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

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REVISION HISTORY

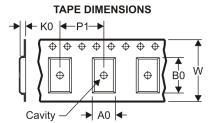
CI	hanges from Original (February 2010) to Revision A	Page
•	Deleted the Package Marking Information section	

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





_		
	Α0	Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
Γ	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17308Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17308Q3	SON	DQG	8	2500	335.0	335.0	32.0

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